

SI3446DV

Single N-Channel, 2.5V Specified PowerTrench MOSFET

General Description

This N-Channel 2.5V specified MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

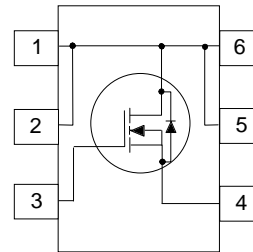
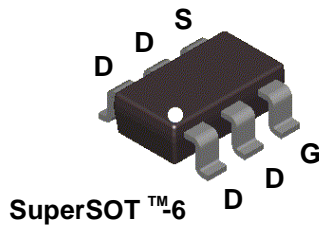
These devices have been designed to offer exceptional power dissipation in a very small footprint compared with bigger SO-8 and TSSOP-8 packages.

Applications

- DC/DC converter
- Load switch
- Battery Protection

Features

- 6.2 A, 20 V. $R_{DS(on)} = 0.024 \Omega @ V_{GS} = 4.5 V$
 $R_{DS(on)} = 0.032 \Omega @ V_{GS} = 2.5 V$
- Fast switching speed.
- Low gate charge (10.5nC typical).
- High performance trench technology for extremely low $R_{DS(on)}$.
- SuperSOT™-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	SI3446DV	
V _{DSS}	Drain-Source Voltage	20	V
V _{GSS}	Gate-Source Voltage	±12	V
I _D	Drain Current - Continuous (Note 1a)	6.2	A
	Drain Current - Pulsed	20	
P _D	Power Dissipation for Single Operation (Note 1a) (Note 1b)	1.6	W
		0.8	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)	78	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case (Note 1)	30	°C/W

Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
.637	FDC637AN	7"	8mm	3000 units

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		14		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}$			1	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 12\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -12\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	0.4	0.82	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 125°C		-3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 4.5\text{ V}, I_D = 6.2\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 6.2\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = 2.5\text{ V}, I_D = 5.2\text{ A}$		0.019 0.028 0.025	0.024 0.041 0.032	Ω
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 4.5\text{ V}, V_{DS} = 5\text{ V}$	10			A
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 6.2\text{ A}$		7.4		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		1125		pF
C_{oss}	Output Capacitance			290		pF
C_{riss}	Reverse Transfer Capacitance			145		pF

Switching Characteristics (Note 2)

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 10\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 4.5\text{ V}, R_{GEN} = 6\ \Omega$		9	18	ns
t_r	Turn-On Rise Time			13	24	ns
$t_{d(off)}$	Turn-Off Delay Time			26	42	ns
t_f	Turn-Off Fall Time			11	20	ns
Q_g	Total Gate Charge	$V_{DS} = 5\text{ V}, I_D = 6.2\text{ A},$ $V_{GS} = 4.5\text{ V}$		10.5	16	nC
Q_{gs}	Gate-Source Charge			1.5		nC
Q_{gd}	Gate-Drain Charge			2.2		nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current				1.3	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 1.3\text{ A}$ (Note 2)		0.7	1.2	V

Notes:

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.
 - 78°C/W when mounted on a 1.0 in^2 pad of 2 oz. copper.
 - 156°C/W when mounted on a minimum pad of 2 oz. copper.
- Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

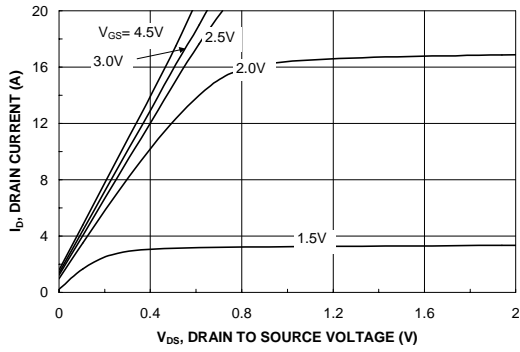


Figure 1. On-Region Characteristics.

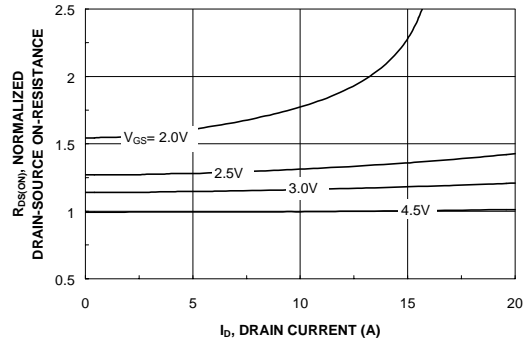


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

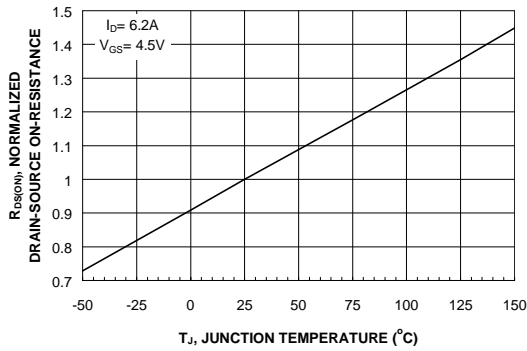


Figure 3. On-Resistance Variation with Temperature.

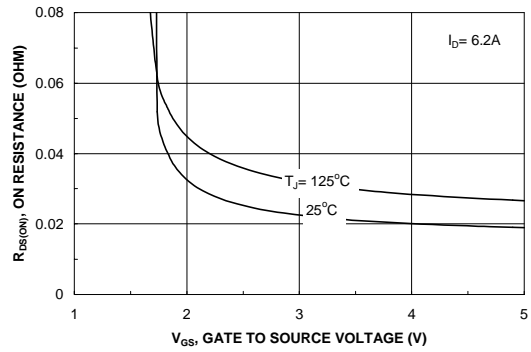


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

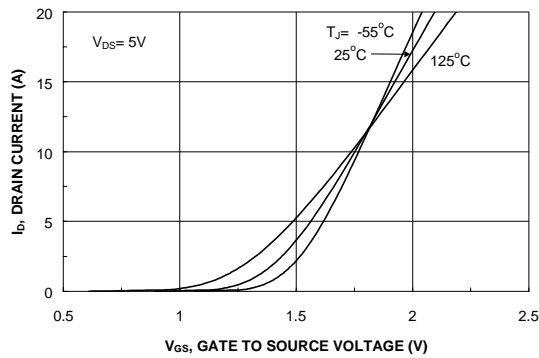


Figure 5. Transfer Characteristics.

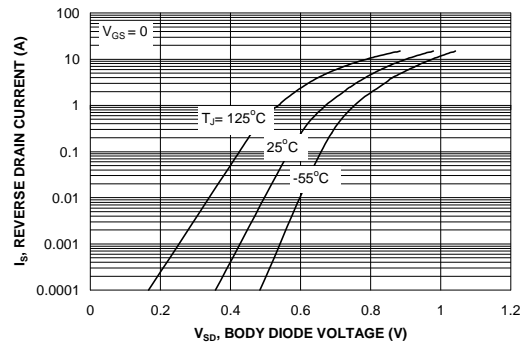


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

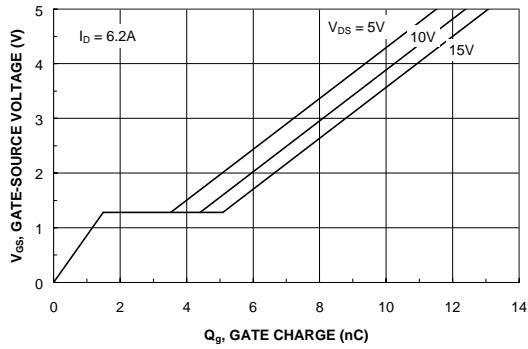


Figure 7. Gate-Charge Characteristics

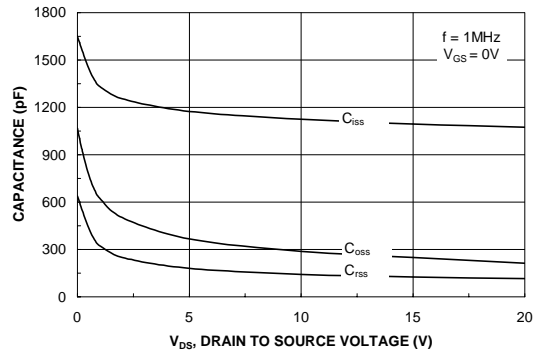


Figure 8. Capacitance Characteristics

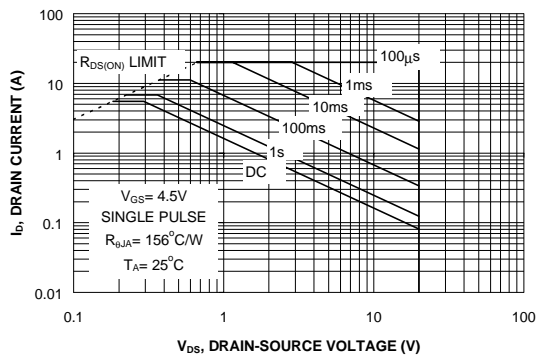


Figure 9. Maximum Safe Operating Area

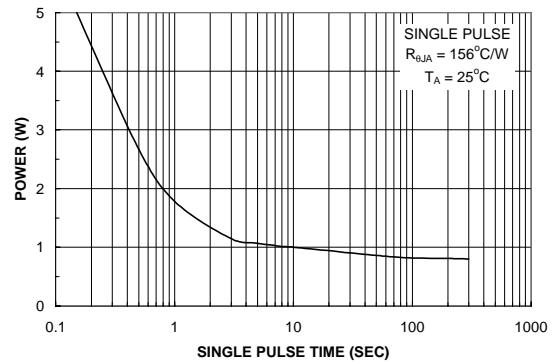


Figure 10. Single Pulse Maximum Power Dissipation

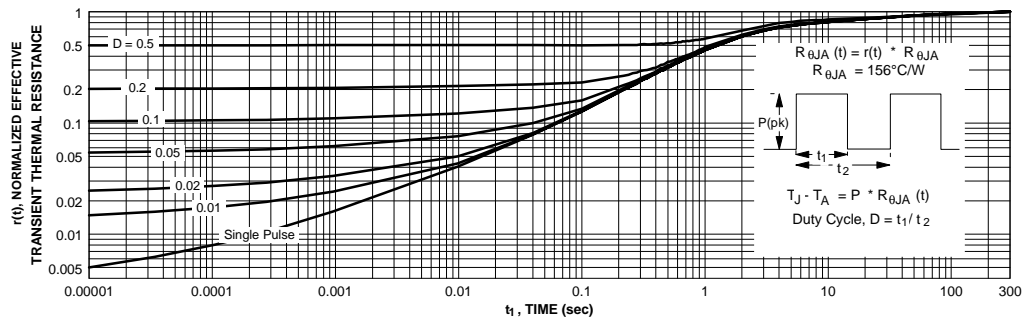


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

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